



Case study: How ESD could generate Electro Magnetic issues



Agenda

- ESD Standard
- ESD Protection
- Case of Study





Types of Overvoltage: Classification



 Natural phenomena (eg: indirect lightning strikes)

EN 61000-4-5
 High Energy Surges

 Industrial discharge (eg: switching off inductive loads)



EN 61000-4-4
 Electric Fast Transient (E.F.T.)

 Electro-Static-Discharge (eg: between humans and materials)



 EN 61000-4-2 ElectroStatic Discharge (E.S.D.)

EU's transient immunity standards for commercial products: The product must continue to operate as intended, without degradation or loss of function after the transient immunity test.

Types of overvoltage: characteristics of High-Voltage Transients



Transient	Voltage	Current	Rise Time	Pulse Width	Pulse Energy	
Surge	0,5-2,0 kV	100-1000 A	1,25 µs	50 µs	10-80 J	
EFT (Single)	0,5-2,0 kV	10-100 A	5 ns	50 ns	4 mJ	
EFT (Burst)	0,5-2,0 kV	10-100 A	n/a	15 ms	100-1000 mJ	
ESD (Contact)	2,0-8,0 kV	7,5-30 A	1 ns	100 ns	1-10 mJ	
			Γ	Key Parameter		

Types of ESD event: main characteristics





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HBM: Specification

- Surge Test Generator is able to produce:
- Contact discharge/Air discharge
- 10 positive and 10 negative strikes (int. std)
- Starting from lower level of pulse voltage.









with values for EN 61000-4-2 => Rs=50-100MΩ, Cb=150pF, Rb=330Ω, RDUT= 2Ω

HBM: Different levels I-V pulses



IEC 61000-4-2 Voltage Levels and Current amount during a strike

Level	Contact	Discharge	Air Discharge				
	Test Voltage kV	Peak Current (A) IEC 61000-4-2	Test Voltage kV	Peak Current (A) IEC 61000-4-2			
1	2	7.5	2	7.5			
2	4	15	4	15			
3	6	22.5	8	30			
4	8	30	15	-			
Χ*	Special	Special	Special	Special			

ESD protection: Diodes and Zener diodes



- A Diode is an electrical component, which lets pass current only in one direction and blocks current in reverse direction
- Z-Diodes have same behavior in forward direction, but in reverse direction they get conducting at defined voltage



ESD protection: Inside Silicon



- During ESD event superficial current capability of Si-device is not enought
- Only using vertical parasitic BJT an ESD protection can be efficient
- An ESD «passive» protection, works in «snap back» configuration



ESD protection: Snap Back Behavior













ESD protection : Diodes and Zener diodes



- Zener Diodes or TVS Diodes are connected in reverse direction
- There's no current through the diode due to breakdown voltage is not exceeded
- If voltage is larger than breakdown voltage there is current through diode







ESD: Topologies (USB 2.0)







ESD: Selection process



- ESD suppressor differ from SMD varistor in their lower and specified capacitance:
 - 1. Determine the Operating Voltage Checking the typical application
 - 2. Checking the max clamping voltage
 - 3. Selection of the correct value of capacitance



Case of Study: General Information



Application: Industrial

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• Metering system for electrical signal (temperature, light, ...)





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Case of Study: ESD Protection Selection



- Electric Parameter:
 - Line frequency: 500 kHz
 - Line Voltage: 5V

Order Code 🔶	SPEC	Downloads	V _{DC} -	l_{Leak} 	V _{Clamp typ.} (V)	V _{ESD Air} ≑	R _{ISO}		Application \$	Design Kit	Samples
82357050100	POF	STP ALT EAG ZUK IGS CDS	5	1	60	15	10	MΩ	USB 1.1 RS-232 LAN 10 Mbit	-	1 \ *
82357050220	POF	STP ALT EAG ZUK IGS CDS	5	1	55	15	10	MΩ	-	823999	1 \₩
82357050330	POP	STP ALT EAG ZUK IGS CDS	5	1	55	15	10	MΩ	RS-422	823999	1 \ !
82357050560	PDF	STP ALT EAG ZUK IGS CDS	5	1	55	15	10	MΩ	RS-485 IrDA 1.0	-	1 \ ± ∕
82356050050	PEF	STP ALT EAG ZUK IGS CDS	5	1	75	15	10	MΩ	USB 1.1 USB 2.0	744999 823999	1 \+
82356050100	POF	STP ALT EAG ZUK IGS CDS	5	1	60	15	10	MΩ	-	-	1 \₩
82356050220	POP	STP ALT EAG ZUK IGS CDS	5	1	55	15	10	MΩ	-	823999	1 \ ! ;
82356050560	POF	STP ALT EAG ZUK IGS CDS	5	1	55	15	10	MΩ	-	-	1 \ ! ;
82356050101	POP	STP ALT EAG ZUK IGS CDS	5	1	55	15	10	MΩ	RS-485 Sensors	823999	1 \ ! ;





WE-TVS TVS Diode – Standard Series

 $V_{DC}~5~to~20~V~|~V_{ESD~Contact}~10~to~30~kV~|~V_{ESD~Air}~16~to~30~kV$



WE-TVS TVS Diode – High Speed Series $V_{DC} \hspace{0.1cm} 3.3 \hspace{0.1cm} \text{to} \hspace{0.1cm} 5 \hspace{0.1cm} \text{V} \hspace{0.1cm} \mid \hspace{0.1cm} V_{ESD \hspace{0.1cm} Contact} \hspace{0.1cm} 8 \hspace{0.1cm} \text{to} \hspace{0.1cm} 24 \hspace{0.1cm} \text{kV} \hspace{0.1cm} \mid \hspace{0.1cm} V_{ESD \hspace{0.1cm} Air} \hspace{0.1cm} \hspace{0.1cm} \hspace{0.1cm} 15 \hspace{0.1cm} \text{to} \hspace{0.1cm} 30 \hspace{0.1cm} \text{kV}$

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WE-TVS TVS Diode – Super Speed Series

 V_{DC} 1.2 to 5 V \mid $V_{ESD\ Contact}$ 8 to 15 kV \mid $V_{ESD\ Air}$ 15 to 16 kV



WE-VE ESD Suppressor V_{DC} 5 to 24 V | V_{ESD Air} 15 kV



WE-VE ULC ESD Suppressor V_{DC} 5 to 12 V | V_{ESD Air} 15 kV



 WE-VE femtoF
 NEW

 V_{DC} 6 to 26 V | V_{ESD Contact} 8 kV | V_{ESD Air} 15 kV



WE-VEA ESD Suppressor-Array



HBM Spice Simulation: Time Domain





Simulation using LTSpice®

- ESD pulses simulated using a current source reproducing IEC 61000-4-2 (HBM)
- Analysis focused at frequencies between 500MHz and 10GHz

HBM Spice Simulation: Frequency Domain (FFT)





HBM Spice Simulation: High Frequency Attenuation



- To reduce high frequency noise 2 ways are possible:
 - Filtering the noise on the cable before it bacames radiation
 - Inductor and Capacitor
 - Ferrite



- Filtering the noise alter radiation using shielding material
 - Conductive shielding
 - Magnetic shielding



CUSTOMIZABLE PRODUCT SERIES



Magnetic Shield with Ferrite: Losses







try to align with the incoming magnetic field. Energy is lost through mechanical torque and phase delay.

Magnetic Shield with Ferrite: Reflection







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Electric Shield with Metal





An incoming EM wave will generate eddy currents on the shield. This means the energy of the EM wave is converted into electric eddy currents.

Eddy current produces an opposing field to cancel the incident field.



Need a connection to ground
High effectiveness in wide frequency range
High attenuation in wide frequancy

No connection to ground
Attenuation is limited in frequency
Attenuation is dependent on width of material

HBM Spice Simulation: Wire Attenuation



- Preferred to use a ferrite solution than LC filter because the ground connection was very far
- Use of <u>RedExpert</u> to find the correct p/n
- Primary Parameters:
 - Rated Current: 2A
 - Pulsed Current: 30A @ 10ns
 - High Attenuation @f> 1GHz
 - Size 0805

NB: The ferromagnetic material with high permeability dissipate enery into heat and it does not need ground connection to «divert»

HBM Spice Simulation: Wire Attenuation





HBM Spice Simulation: Shielding Attenuation



- Preferred to use a ferrite solution than metal because the ground connection was very far
- Use of <u>www.we-online.com</u> to find the correct p/n
- Primary Parameters:
 - Attenuation @f > 500MHz



Conclusions



- Both solutions are effective
- For assembly purposes the final solution was using wire components and not shielding material





